



TANCERAM[®] chip capacitors can replace tantalum capacitors in many applications and offer several key advantages over traditional tantalums. Because Tanceram® capacitors exhibit extremely low ESR, equivalent circuit performance can often be achieved using considerably lower capacitance values. Low DC leakage reduces current drain, extending the battery life of portable products. Tancerams® high DC breakdown voltage ratings offer improved reliability and eliminate large voltage de-rating common when designing with tantalums.

ADVANTAGES

Low ESR

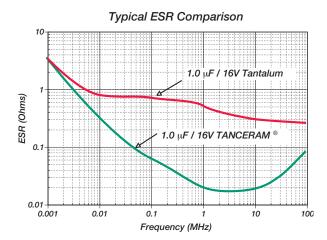
APPLICATIONS

- Higher Surge Voltage
- **Reduced CHIP Size**
- Higher Insulation Resistance
 Higher Ripple Current
- Low DC Leakage Non-polarized Devices
- Improved Reliability

Switching Power Supply Smoothing (Input/Output)

DC/DC Converter Smoothing (Input/Output)

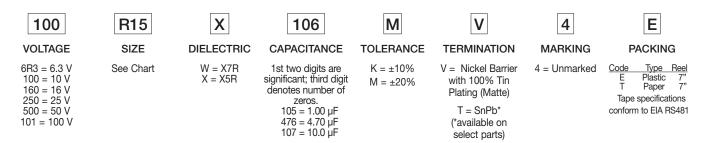
- Backlighting Inverters
- General Digital Circuits



How to Order TANCERAM®

Typical Breakdown Voltage Comparison 100% 1.0 µF / 16V Tantalum 75% Distribution 50% 1.0 uF / 16V TANCERAM % 25% 0% 100 200 300 400 500 DC Breakdown Voltage

Part number written: 100R15X106MV4E







CASE SIZE

CAPACITANCE SELECTION

EIA	/ JDI		Inches	(mm)	VDC	1.0	μF	2.2	μF	3.3	μF	4.7	μF	10	μF	22	μF	47	μF	100) µF
	402 07	L W T EB	.040 ±.004 .020 ±.004 .025 Max. .008 ±.004	(1.02 ±.10) (0.51 ±.10) (0.64) (0.20±.10)	16 10 6.3										DIELECTRIC W (X7R)						
	603 14	L W T EB	.063 ±.008 .032 ±.008 .035 Max. .010±.005	(1.60 ±.20) (0.81 ±.20) (0.89) (.25±.13)	25 16 10 6.3										X (X5R)						
	305 15	L W T EB	.080 ±.010 .050 ±.010 .060 Max. .020±.010	(2.03 ±.25) (1.27 ±.25) (1.52) (0.51±.25)	50 25 16 10 6.3																
	206 18	L W T EB	.125 ±.010 .062 ±.010 .070 Max. .020 +.015-0.01	(3.17 ±.25) (1.57 ±.25) (1.78) (0.51+.3825)	100 50 35 25 16 10 6.3																
	210 41	L W T EB	.125 ±.010 .095 ±.010 .110 Max. .020 +.015010	(3.18 ±.25) (2.41 ±.25) (2.8) (0.51+.3825)	100 50 35 25 16 10 6.3																
	312 43	L W T EB	.175 ±.010 .125 ±.010 .140 Max. .035 ±.020	(4.45 ±.25) (3.17 ±.25) (3.55) (0.89 ±0.51)	100 50 25 16 10 6.3																

ELECTRICAL CHARACTERISTICS

Dielectric:	X7R	X5R					
Temperature Coefficient:	±15% (-55 to +125°C)	±15% (-55 to +85°C)					
Dissipation Factor:	For ≥ 50 VDC: 5% max. For ≤ 25 VDC: 10% max.	For ≥ 50 VDC: 5% max. For ≤ 25 VDC: 10% max.					
Insulation Resistance (Min. @ 25°C, Wvdc)	100 ΩF or 10 G $\Omega,$ whichever is less						
Dielectric Strength:	2.5 X WVDC, 25°C, 50mA max.						
Test Conditions:	Capacitance values < 22 μF : 1.0kHz±50Hz @ 1.0±0.2 Vrms Capacitance values > 22 μF : 120Hz±10Hz @ 0.5V±0.1 Vrms						
Other:	See page 35 for additional dielectric specifications.						



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D55342E07B523DR-T/R NCA1206X7R103K50TRPF NCA1206X7R104K16TRPF NIN-FB391JTRF NIN-FC2R7JTRF NMC0402NPO220J50TRPF NMC0402X5R105K6.3TRPF NMC0402X5R224K6.3TRPF NMC0402X7R103J25TRPF NMC0402X7R153K16TRPF NMC0603NPO330G50TRPF NMC0603NPO331F50TRPF NMC0603X5R475M6.3TRPF NMC0805NPO220J100TRPF NMC0805NPO270J50TRPF NMC0603NPO681F50TRPF NMC0805NPO820J50TRPF NMC0805X7R224K25TRPF NMC1206X7R102K50TRPF NMC1210Y5V105Z50TRPLPF NMC-H0805X7R472K250TRPF NMC-L0402NPO7R0C50TRPF NMC12063NPO2R2B50TRPF NMC-Q0402NPO8R2D200TRPF C1206C101J1GAC C1608C0G2A221J C1608X7R1E334K C2012C0G2A472J 2220J2K00562KXT KHC201E225M76N0T00 1812J2K00332KXT CCR06CG153FSV CDR14BP471CJUR CDR31BX103AKWR CDR33BX683AKUS CGA2B2C0G1H010C CGA2B2C0G1H040C CGA2B2C0G1H050C CGA2B2C0G1H060D CGA2B2C0G1H070D CGA2B2C0G1H120J CGA2B2C0G1H151J CGA2B2C0G1H07C CGA2B2C0G1H050C CGA2B2C0G1H390J CGA2B2C0G1H391J CGA2B2C0G1H3R3C CGA2B2C0G1H680J CGA2B2C0G1H6R8D CGA2B2C0G1H820J